

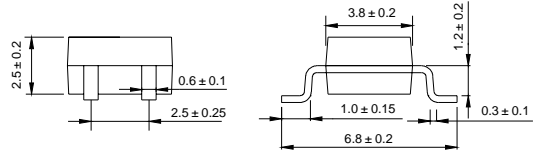
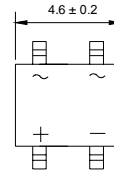
MBS

Features

- ◇ I_o 1.0A
- ◇ V_{RRM} 20V~100V
- ◇ Schottky chip
- ◇ High surge forward current capability
- ◇ Low VF

Applications

- ◇ General purpose 1 phase Bridge
- ◇ rectifier applications



Dimensions in millimeters

Limiting Values (Absolute Maximum Rating)

Item	Symbol	Unit	Conditions	MB					
				12S	14S	16S	18S	110S	
Repetitive Peak Reverse Voltage	V_{RRM}	V		20	40	60	80	100	
Average Rectified Output Current	I_o	A	60Hz sine wave, R-load, $T_a=25^\circ\text{C}$	On alumina substrate	1.0				
				On glass-epoxi substrate	0.8				
Surge(Non-repetitive)Forward Current	I_{FSM}	A	60Hz sine wave, 1 cycle, $T_j=25^\circ\text{C}$		40				
Current Squared Time	I^2t	A^2S	$1\text{ms} \leq t < 8.3\text{ms}$ $T_j=25^\circ\text{C}$, Rating of per diode		6.6				
Storage Temperature	T_{stg}	$^\circ\text{C}$	-55 ~+150						
Junction Temperature	T_j	$^\circ\text{C}$	-55 ~+150						

Electrical Characteristics ($T_a=25^\circ\text{C}$ Unless otherwise specified)

Item	Symbol	Unit	Test Condition	Max		
Peak Forward Voltage	V_{FM}	V	$I_{FM}=0.5\text{A}$, Pulse measurement, Rating of per diode	0.55	0.65	0.85
Peak Reverse Current	I_{RRM}	mA	$V_{RM}=V_{RRM}$, Pulse measurement, Rating of per diode	0.5		
Thermal Resistance	$R_{\theta J-A}$	$^\circ\text{C/W}$	Between junction and ambient, On alumina substrate	76		
			Between junction and ambient, On glass-epoxi substrate	134		
	$R_{\theta J-L}$		Between junction and lead	20		

Characteristics(Typical)

FIG1:Io-Ta Curve

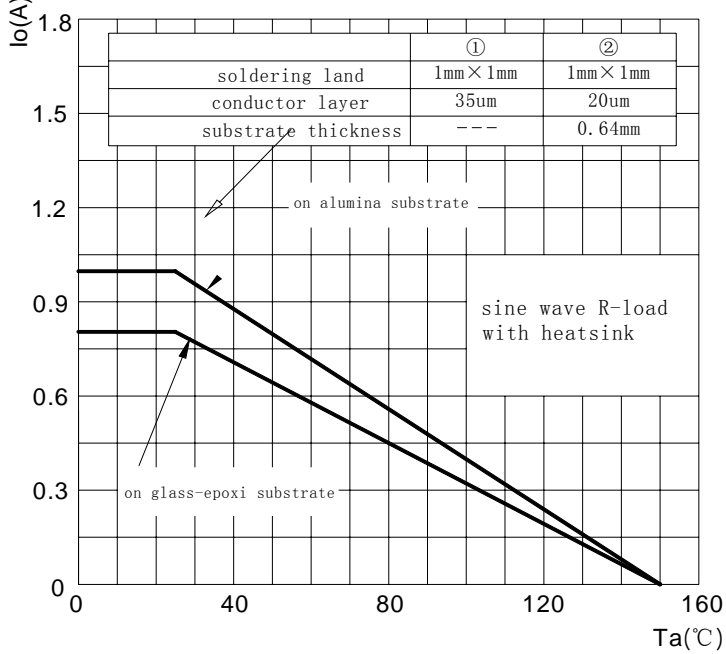


FIG2:Surge Forward Current Capacity

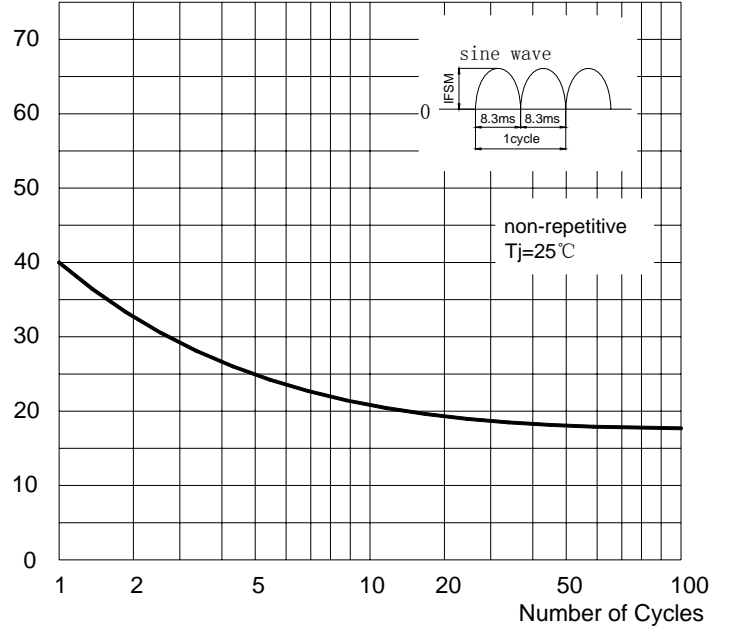


FIG3: Forward Voltage

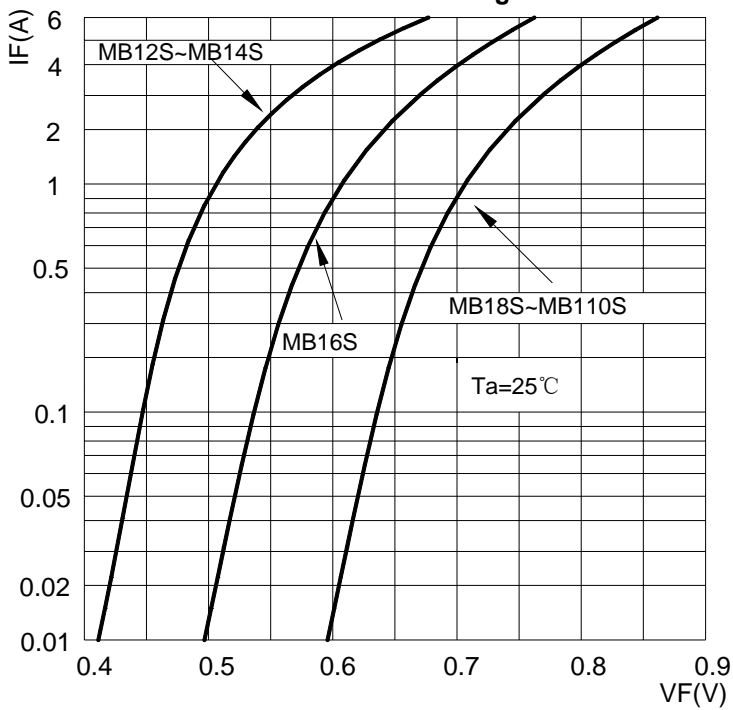


FIG4:Typical Reverse Characteristics

